

Description

Semicoa Semiconductors offers:

- Screening and processing per MIL-PRF-19500 Appendix E
- JAN level (2N5582J)
- JANTX level (2N5582JX)
- JANTXV level (2N5582JV)
- QCI to the applicable level
- 100% die visual inspection per MIL-STD-750 method 2072 for JANTXV
- Radiation testing (total dose) upon request

Please contact Semicoa for special configurations
www.SEMICOA.com or (714) 979-1900

Applications

- General purpose switching
- Low power
- NPN silicon transistor



Features

- Hermetically sealed TO-46 metal can
- Also available in chip configuration
- Chip geometry 0400
- Reference document:
MIL-PRF-19500/423

Benefits

- Qualification Levels: JAN, JANTX, and JANTXV
- Radiation testing available

Absolute Maximum Ratings		T _C = 25°C unless otherwise specified	
Parameter	Symbol	Rating	Unit
Collector-Emitter Voltage	V _{CEO}	50	Volts
Collector-Base Voltage	V _{CB0}	75	Volts
Collector Current, Continuous	I _C	800	mA
Power Dissipation, T _A = 25°C Derate linearly above 25°C	P _T	500 2.86	mW mW/°C
Power Dissipation, T _C = 25°C Derate linearly above 25°C	P _T	2 11.43	W mW/°C
Operating Junction Temperature	T _J	-55 to+200	°C
Storage Temperature	T _{STG}	-55 to+200	°C

ELECTRICAL CHARACTERISTICS

characteristics specified at $T_A = 25^\circ\text{C}$

Off Characteristics

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 10\text{ mA}$	50			Volts
Collector-Base Cutoff Current	I_{CBO1}	$V_{CB} = 75\text{ Volts}$			10	μA
	I_{CBO2}	$V_{CB} = 60\text{ Volts}$			10	nA
	I_{CBO3}	$V_{CB} = 60\text{ Volts}, T_A = 150^\circ\text{C}$			10	μA
Emitter-Base Cutoff Current	I_{EBO1}	$V_{EB} = 6\text{ Volts}$			10	μA
	I_{EBO2}	$V_{EB} = 4\text{ Volts}$			10	nA

On Characteristics

Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2.0\%$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
DC Current Gain	h_{FE1}	$I_C = 0.1\text{ mA}, V_{CE} = 10\text{ Volts}$	50			
	h_{FE2}	$I_C = 1\text{ mA}, V_{CE} = 10\text{ Volts}$	75			
	h_{FE3}	$I_C = 10\text{ mA}, V_{CE} = 10\text{ Volts}$	100			
	h_{FE4}	$I_C = 150\text{ mA}, V_{CE} = 10\text{ Volts}$	100		300	
	h_{FE5}	$I_C = 500\text{ mA}, V_{CE} = 10\text{ Volts}$	30			
	h_{FE6}	$I_C = 10\text{ mA}, V_{CE} = 10\text{ Volts}$ $T_A = -55^\circ\text{C}$	35			
Base-Emitter Saturation Voltage	V_{BEsat1}	$I_C = 150\text{ mA}, I_B = 15\text{ mA}$			1.2	Volts
	V_{BEsat2}	$I_C = 500\text{ mA}, I_B = 50\text{ mA}$			2.0	Volts
Collector-Emitter Saturation Voltage	V_{CEsat1}	$I_C = 150\text{ mA}, I_B = 15\text{ mA}$			0.3	Volts
	V_{CEsat2}	$I_C = 500\text{ mA}, I_B = 50\text{ mA}$			1.0	Volts

Dynamic Characteristics

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Magnitude – Common Emitter, Short Circuit Forward Current Transfer Ratio	$ h_{FE} $	$V_{CE} = 20\text{ Volts}, I_C = 50\text{ mA}, f = 100\text{ MHz}$	2.5			
Small Signal Short Circuit Forward Current Transfer Ratio	h_{FE}	$V_{CE} = 10\text{ Volts}, I_C = 1\text{ mA}, f = 1\text{ kHz}$	50			
Open Circuit Output Capacitance	C_{OBO}	$V_{CB} = 10\text{ Volts}, I_E = 0\text{ mA}, 100\text{ kHz} < f < 1\text{ MHz}$			8	pF
Open Circuit Input Capacitance	C_{IBO}	$V_{EB} = 0.5\text{ Volts}, I_C = 0\text{ mA}, 100\text{ kHz} < f < 1\text{ MHz}$			25	pF

Switching Characteristics

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Saturated Turn-On Time	t_{ON}				35	ns
Saturated Turn-Off Time	t_{OFF}				300	ns